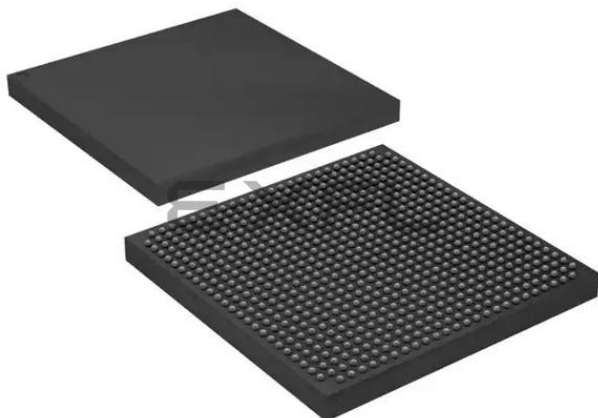




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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

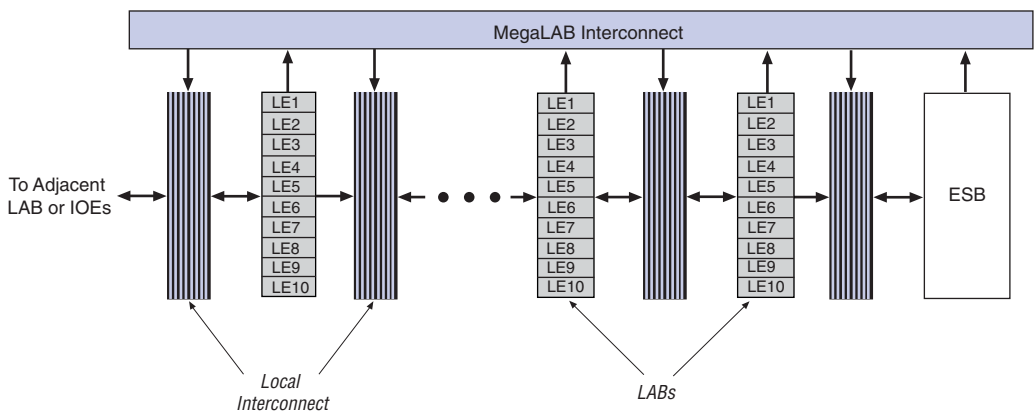
Details

Product Status	Obsolete
Number of LABs/CLBs	1664
Number of Logic Elements/Cells	16640
Total RAM Bits	212992
Number of I/O	488
Number of Gates	1052000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k400cf672c8

MegaLAB Structure

APEX 20KC devices are constructed from a series of MegaLAB™ structures. Each MegaLAB structure contains 16 logic array blocks (LABs), one ESB, and a MegaLAB interconnect, which routes signals within the MegaLAB structure. In EP20K1000C devices, MegaLAB structures contain 24 LABs. Signals are routed between MegaLAB structures and I/O pins via the FastTrack interconnect. In addition, edge LABs can be driven by I/O pins through the local interconnect. Figure 2 shows the MegaLAB structure.

Figure 2. MegaLAB Structure

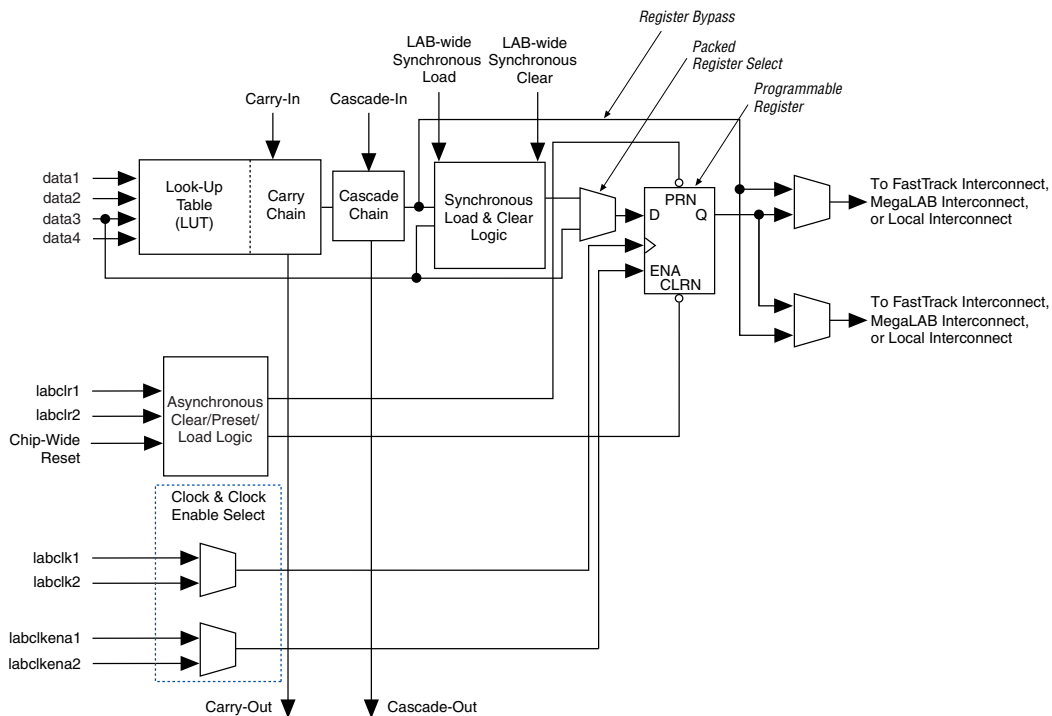


Logic Array Block

Each LAB consists of 10 LEs, the LEs' associated carry and cascade chains, LAB control signals, and the local interconnect. The local interconnect transfers signals between LEs in the same or adjacent LABs, IOEs, or ESBs. The Quartus II Compiler places associated logic within an LAB or adjacent LABs, allowing the use of a fast local interconnect for high performance. Figure 3 shows the APEX 20KC LAB.

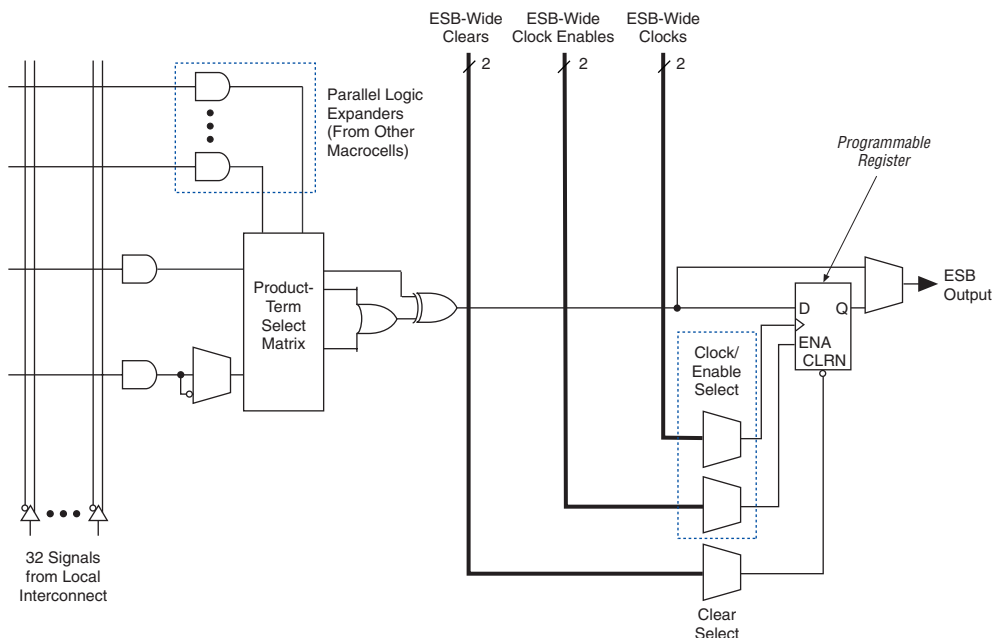
APEX 20KC devices use an interleaved LAB structure. This structure allows each LE to drive two local interconnect areas, minimizing the use of the MegaLAB and FastTrack interconnect and providing higher performance and flexibility. Each LE can drive 29 other LEs through the fast local interconnect.

Figure 5. APEX 20KC Logic Element



Each LE's programmable register can be configured for D, T, JK, or SR operation. The register's clock and clear control signals can be driven by global signals, general-purpose I/O pins, or any internal logic. For combinatorial functions, the register is bypassed and the output of the LUT drives the outputs of the LE.

Each LE has two outputs that drive the local, MegaLAB, or FastTrack interconnect routing structure. Each output can be driven independently by the LUT's or register's output. For example, the LUT can drive one output while the register drives the other output. This feature, called register packing, improves device utilization because the register and the LUT can be used for unrelated functions. The LE can also drive out registered and unregistered versions of the LUT output.

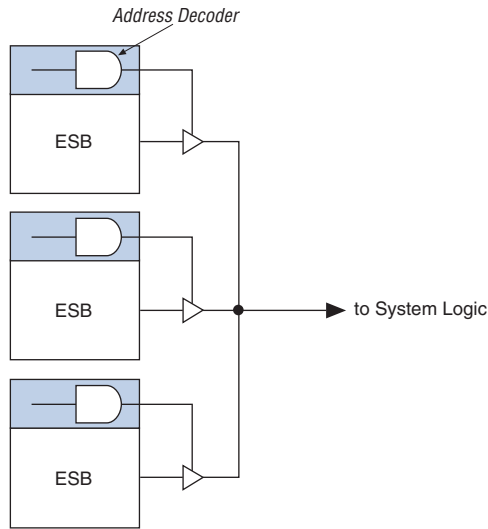
Figure 14. APEX 20KC Macrocell


For registered functions, each macrocell register can be programmed individually to implement D, T, JK, or SR operation with programmable clock control. The register can be bypassed for combinatorial operation. During design entry, the designer specifies the desired register type; the Quartus II software then selects the most efficient register operation for each registered function to optimize resource utilization. The Quartus II software or other synthesis tools can also select the most efficient register operation automatically when synthesizing HDL designs.

Each programmable register can be clocked by one of two ESB-wide clocks. The ESB-wide clocks can be generated from device dedicated clock pins, global signals, or local interconnect. Each clock also has an associated clock enable, generated from the local interconnect. The clock and clock enable signals are related for a particular ESB; any macrocell using a clock also uses the associated clock enable.

If both the rising and falling edges of a clock are used in an ESB, both ESB-wide clock signals are used.

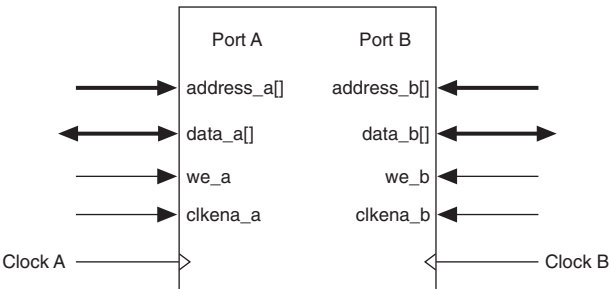
Figure 18. Deep Memory Block Implemented with Multiple ESBs



The ESB implements two forms of dual-port memory: read/write clock mode and input/output clock mode. The ESB can also be used for bidirectional, dual-port memory applications in which two ports read or write simultaneously. To implement this type of dual-port memory, two ESBs are used to support two simultaneous reads or writes.

The ESB can also use Altera megafunctions to implement dual-port RAM applications where both ports can read or write, as shown in [Figure 19](#).

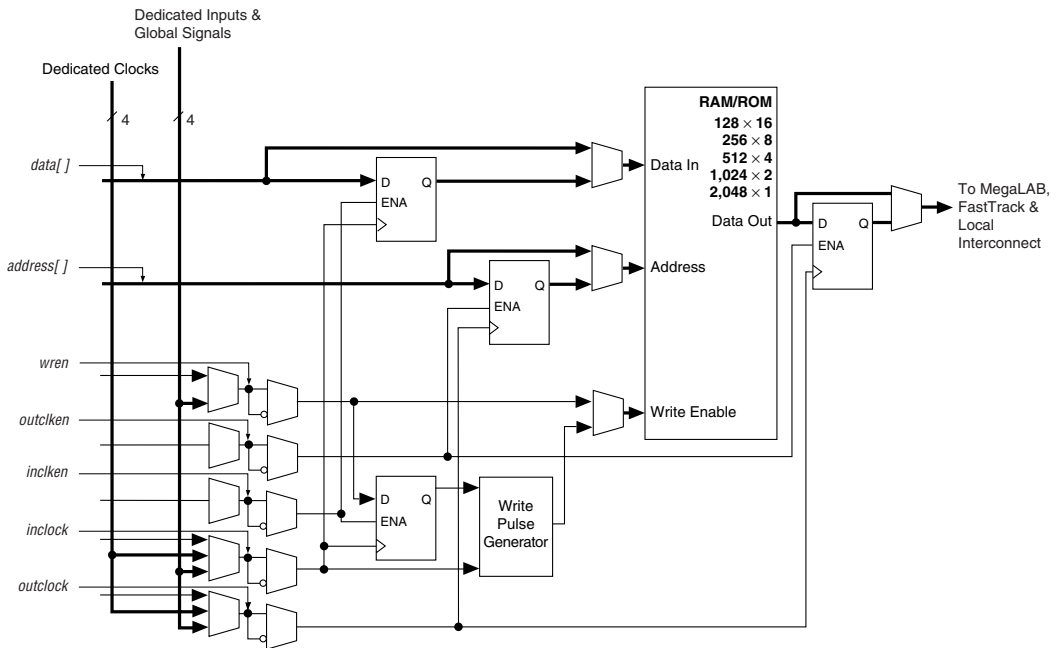
Figure 19. APEX 20KC ESB Implementing Dual-Port RAM



Single-Port Mode

The APEX 20KC ESB also supports a single-port mode, which is used when simultaneous reads and writes are not required. See [Figure 22](#).

Figure 22. ESB in Single-Port Mode *Note (1)*



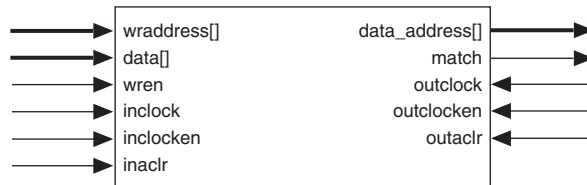
Note to Figure 22:

- (1) All registers can be asynchronously cleared by ESB local interconnect signals, global signals, or the chip-wide reset.

Content-Addressable Memory

In APEX 20KC devices, the ESB can implement CAM. CAM can be thought of as the inverse of RAM. When read, RAM outputs the data for a given address. Conversely, CAM outputs an address for a given data word. For example, if the data FA12 is stored in address 14, the CAM outputs 14 when FA12 is driven into it.

Figure 23. APEX 20KC CAM Block Diagram



CAM can be used in any application requiring high-speed searches, such as networking, communications, data compression, and cache management.

The APEX 20KC on-chip CAM provides faster system performance than traditional discrete CAM. Integrating CAM and logic into the APEX 20KC device eliminates off-chip and on-chip delays, improving system performance.

When in CAM mode, the ESB implements 32-word, 32-bit CAM. Wider or deeper CAM can be implemented by combining multiple CAMs with some ancillary logic implemented in LEs. The Quartus II software combines ESBs and LEs automatically to create larger CAMs.

CAM supports writing “don’t care” bits into words of the memory. The “don’t care” bit can be used as a mask for CAM comparisons; any bit set to “don’t care” has no effect on matches.

The output of the CAM can be encoded or unencoded. When encoded, the ESB outputs an encoded address of the data’s location. For instance, if the data is located in address 12, the ESB output is 12. When unencoded, the ESB uses its 16 outputs to show the location of the data over two clock cycles. In this case, if the data is located in address 12, the 12th output line goes high. When using unencoded outputs, two clock cycles are required to read the output because a 16-bit output bus is used to show the status of 32 words.

The encoded output is better suited for designs that ensure duplicate data is not written into the CAM. If duplicate data is written into two locations, the CAM’s output will be incorrect. If the CAM may contain duplicate data, the unencoded output is a better solution; CAM with unencoded outputs can distinguish multiple data locations.

CAM can be pre-loaded with data during configuration, or it can be written during system operation. In most cases, two clock cycles are required to write each word into CAM. When “don’t care” bits are used, a third clock cycle is required.

Implementing Logic in ROM

In addition to implementing logic with product terms, the ESB can implement logic functions when it is programmed with a read-only pattern during configuration, creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of ESBs. The large capacity of ESBs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or distributed RAM blocks. Parameterized functions such as LPM functions can take advantage of the ESB automatically. Further, the Quartus II software can implement portions of a design with ESBs where appropriate.

Programmable Speed/Power Control

APEX 20KC ESBs offer a high-speed mode that supports very fast operation on an ESB-by-ESB basis. When high speed is not required, this feature can be turned off to reduce the ESB's power dissipation by up to 50%. ESBs that run at low power incur a nominal timing delay adder. This Turbo Bit™ option is available for ESBs that implement product-term logic or memory functions. An ESB that is not used will be powered down so that it does not consume DC current.

Designers can program each ESB in the APEX 20KC device for either high-speed or low-power operation. As a result, speed-critical paths in the design can run at high speed, while the remaining paths operate at reduced power.

I/O Structure

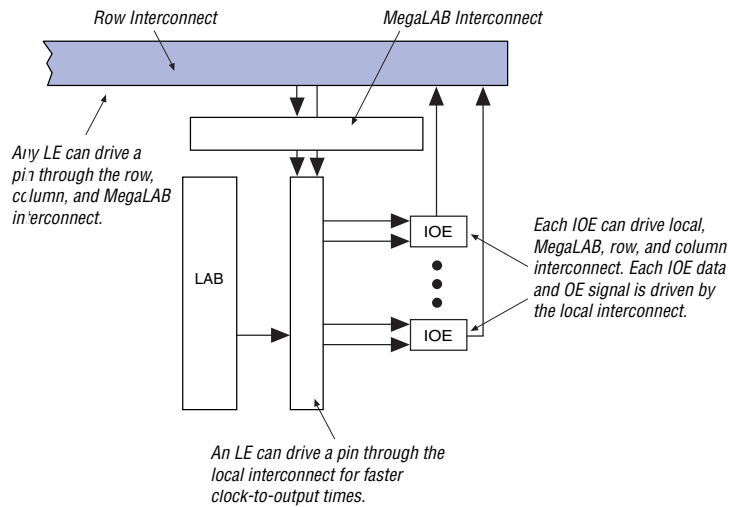
The APEX 20KC IOE contains a bidirectional I/O buffer and a register that can be used either as an input register for external data requiring fast setup times or as an output register for data requiring fast clock-to-output performance. IOEs can be used as input, output, or bidirectional pins.

Notes to Figure 25:

- (1) This programmable delay has four settings: off and three levels of delay.
- (2) The output enable and input registers are LE registers in the LAB adjacent to the bidirectional pin.

Each IOE drives a row, column, MegaLAB, or local interconnect when used as an input or bidirectional pin. A row IOE can drive a local, MegaLAB, row, and column interconnect; a column IOE can drive the column interconnect. **Figure 26** shows how a row IOE connects to the interconnect.

Figure 26. Row IOE Connection to the Interconnect



IEEE Std. 1149.1 (JTAG) Boundary-Scan Support

All APEX 20KC devices provide JTAG BST circuitry that complies with the IEEE Std. 1149.1-1990 specification. JTAG boundary-scan testing can be performed before or after configuration, but not during configuration. APEX 20KC devices can also use the JTAG port for configuration with the Quartus II software or with hardware using either Jam Files (**.jam**) or Jam Byte-Code Files (**.jbc**). Finally, APEX 20KC devices use the JTAG port to monitor the logic operation of the device with the SignalTap embedded logic analyzer. APEX 20KC devices support the JTAG instructions shown in [Table 13](#).

Table 13. APEX 20KC JTAG Instructions

JTAG Instruction	Description
SAMPLE/PRELOAD	Allows a snapshot of signals at the device pins to be captured and examined during normal device operation, and permits an initial data pattern to be output at the device pins. Also used by the SignalTap embedded logic analyzer.
EXTEST	Allows the external circuitry and board-level interconnections to be tested by forcing a test pattern at the output pins and capturing test results at the input pins.
BYPASS	Places the 1-bit bypass register between the TDI and TDO pins, which allows the BST data to pass synchronously through selected devices to adjacent devices during normal device operation.
USERCODE	Selects the 32-bit USERCODE register and places it between the TDI and TDO pins, allowing the USERCODE to be serially shifted out of TDO.
IDCODE	Selects the IDCODE register and places it between TDI and TDO, allowing the IDCODE to be serially shifted out of TDO.
ICR Instructions	Used when configuring an APEX 20KC device via the JTAG port with a MasterBlaster™ or ByteBlasterMV™ download cable, or when using a Jam File or Jam Byte-Code File via an embedded processor.
SignalTap Instructions	Monitors internal device operation with the SignalTap embedded logic analyzer.

Table 20. APEX 20KC Device Capacitance *Note (10)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	$V_{IN} = 0\text{ V}$, $f = 1.0\text{ MHz}$		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	$V_{IN} = 0\text{ V}$, $f = 1.0\text{ MHz}$		12	pF
C_{OUT}	Output capacitance	$V_{OUT} = 0\text{ V}$, $f = 1.0\text{ MHz}$		8	pF

Notes to Tables 17 through 20:

- (1) See the *Operating Requirements for Altera Devices Data Sheet*.
- (2) Minimum DC input is -0.5 V . During transitions, the inputs may undershoot to -2.0 V or overshoot to 4.6 V for input currents less than 100 mA and time periods shorter than 20 ns .
- (3) Numbers in parentheses are for industrial-temperature-range devices.
- (4) Maximum V_{CC} rise time is 100 ms , and V_{CC} must rise monotonically.
- (5) All pins, including dedicated inputs, clock, I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
- (6) Typical values are for $T_A = 25^\circ\text{ C}$, $V_{CCINT} = 1.8\text{ V}$, and $V_{CCIO} = 1.8\text{ V}$, 2.5 V or 3.3 V .
- (7) These values are specified under the APEX 20KC device recommended operating conditions, shown in [Table 18 on page 55](#).
- (8) This value is specified for normal device operation. The value may vary during power-up.
- (9) Pin pull-up resistance values will be lower if an external source drives the pin higher than V_{CCIO} .
- (10) Capacitance is sample-tested only.

Tables 21 through 35 list the DC operating specifications for the supported I/O standards. These tables list minimal specifications only; APEX 20KC devices may exceed these specifications.

Table 21. LVTTTL I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Units
V_{CCIO}	Output supply voltage		3.0	3.6	V
V_{IH}	High-level input voltage		2.0	$V_{CCIO} + 0.3$	V
V_{IL}	Low-level input voltage		-0.3	0.8	V
I_I	Input pin leakage current	$V_{IN} = 0\text{ V}$ or 3.3 V	-10	10	μA
V_{OH}	High-level output voltage	$I_{OH} = -12\text{ mA}$, $V_{CCIO} = 3.0\text{ V}$ (1)	2.4		V
V_{OL}	Low-level output voltage	$I_{OL} = 12\text{ mA}$, $V_{CCIO} = 3.0\text{ V}$ (2)		0.4	V

Table 22. LVCMOS I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Units
V_{CCIO}	Power supply voltage range		3.0	3.6	V
V_{IH}	High-level input voltage		2.0	$V_{CCIO} + 0.3$	V
V_{IL}	Low-level input voltage		-0.3	0.8	V
I_I	Input pin leakage current	$V_{IN} = 0\text{ V or }3.3\text{ V}$	-10	10	μA
V_{OH}	High-level output voltage	$V_{CCIO} = 3.0\text{ V}$ $I_{OH} = -0.1\text{ mA (1)}$	$V_{CCIO} - 0.2$		V
V_{OL}	Low-level output voltage	$V_{CCIO} = 3.0\text{ V}$ $I_{OL} = 0.1\text{ mA (2)}$		0.2	V

Table 23. 2.5-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Units
V_{CCIO}	Output supply voltage		2.375	2.625	V
V_{IH}	High-level input voltage		1.7	$V_{CCIO} + 0.3$	V
V_{IL}	Low-level input voltage		-0.3	0.8	V
I_I	Input pin leakage current	$V_{IN} = 0\text{ V or }3.3\text{ V}$	-10	10	μA
V_{OH}	High-level output voltage	$I_{OH} = -0.1\text{ mA (1)}$	2.1		V
		$I_{OH} = -1\text{ mA (1)}$	2.0		V
		$I_{OH} = -2\text{ mA (1)}$	1.7		V
V_{OL}	Low-level output voltage	$I_{OL} = 0.1\text{ mA (2)}$		0.2	V
		$I_{OL} = 1\text{ mA (2)}$		0.4	V
		$I_{OL} = 2\text{ mA (2)}$		0.7	V

Table 24. 1.8-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Units
V_{CCIO}	Output supply voltage		1.7	1.9	V
V_{IH}	High-level input voltage		$0.65 \times V_{CCIO}$	$V_{CCIO} + 0.3$	V
V_{IL}	Low-level input voltage			$0.35 \times V_{CCIO}$	V
I_I	Input pin leakage current	$V_{IN} = 0 \text{ V or } 3.3 \text{ V}$	-10	10	μA
V_{OH}	High-level output voltage	$I_{OH} = -2 \text{ mA (1)}$	$V_{CCIO} - 0.45$		V
V_{OL}	Low-level output voltage	$I_{OL} = 2 \text{ mA (2)}$		0.45	V

Table 25. 3.3-V PCI Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.0	3.3	3.6	V
V_{IH}	High-level input voltage		$0.5 \times V_{CCIO}$		$V_{CCIO} + 0.5$	V
V_{IL}	Low-level input voltage		-0.5		$0.3 \times V_{CCIO}$	V
I_I	Input pin leakage current	$0 < V_{IN} < V_{CCIO}$	-10		10	μA
V_{OH}	High-level output voltage	$I_{OUT} = -500 \mu\text{A}$	$0.9 \times V_{CCIO}$			V
V_{OL}	Low-level output voltage	$I_{OUT} = 1,500 \mu\text{A}$			$0.1 \times V_{CCIO}$	V

Table 32. SSTL-3 Class II Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.0	3.3	3.6	V
V_{TT}	Termination voltage		$V_{REF} - 0.05$	V_{REF}	$V_{REF} + 0.05$	V
V_{REF}	Reference voltage		1.3	1.5	1.7	V
V_{IH}	High-level input voltage		$V_{REF} + 0.2$		$V_{CCIO} + 0.3$	V
V_{IL}	Low-level input voltage		-0.3		$V_{REF} - 0.2$	V
V_{OH}	High-level output voltage	$I_{OH} = -16 \text{ mA}$ (1)	$V_{TT} + 0.8$			V
V_{OL}	Low-level output voltage	$I_{OL} = 16 \text{ mA}$ (2)			$V_{TT} - 0.8$	V

Table 33. HSTL Class I I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		1.71	1.8	1.89	V
V_{TT}	Termination voltage		$V_{REF} - 0.05$	V_{REF}	$V_{REF} + 0.05$	V
V_{REF}	Reference voltage		0.68	0.75	0.90	V
V_{IH}	High-level input voltage		$V_{REF} + 0.1$		$V_{CCIO} + 0.3$	V
V_{IL}	Low-level input voltage		-0.3		$V_{REF} - 0.1$	V
V_{OH}	High-level output voltage	$I_{OH} = -8 \text{ mA}$ (1)	$V_{CCIO} - 0.4$			V
V_{OL}	Low-level output voltage	$I_{OL} = 8 \text{ mA}$ (2)			0.4	V

Table 34. 3.3-V AGP I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.15	3.3	3.45	V
V_{REF}	Reference voltage		$0.39 \times V_{CCIO}$		$0.41 \times V_{CCIO}$	V
V_{IH}	High-level input voltage		$0.5 \times V_{CCIO}$		$V_{CCIO} + 0.5$	V
V_{IL}	Low-level input voltage				$0.3 \times V_{CCIO}$	V
V_{OH}	High-level output voltage	$I_{OUT} = -500 \mu A$	$0.9 \times V_{CCIO}$		3.6	V
V_{OL}	Low-level output voltage	$I_{OUT} = 1,500 \mu A$			$0.1 \times V_{CCIO}$	V
I_I	Input pin leakage current	$0 < V_{IN} < V_{CCIO}$	-10		10	μA

Table 35. CTT I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.0	3.3	3.6	V
V_{TT}/V_{REF} (3)	Termination and reference voltage		1.35	1.5	1.65	V
V_{IH}	High-level input voltage		$V_{REF} + 0.2$			V
V_{IL}	Low-level input voltage				$V_{REF} - 0.2$	V
I_I	Input pin leakage current	$0 < V_{IN} < V_{CCIO}$	-10		10	μA
V_{OH}	High-level output voltage	$I_{OH} = -8 \text{ mA}$ (1)	$V_{REF} + 0.4$			V
V_{OL}	Low-level output voltage	$I_{OL} = 8 \text{ mA}$ (2)			$V_{REF} - 0.4$	V
I_O	Output leakage current (when output is high Z)	$GND \leq V_{OUT} \leq V_{CCIO}$	-10		10	μA

Notes to Tables 21 through 35:

- (1) The I_{OH} parameter refers to high-level output current.
- (2) The I_{OL} parameter refers to low-level output current. This parameter applies to open-drain pins as well as output pins.
- (3) V_{REF} specifies center point of switching range.

Figure 31 shows the output drive characteristics of APEX 20KC devices.

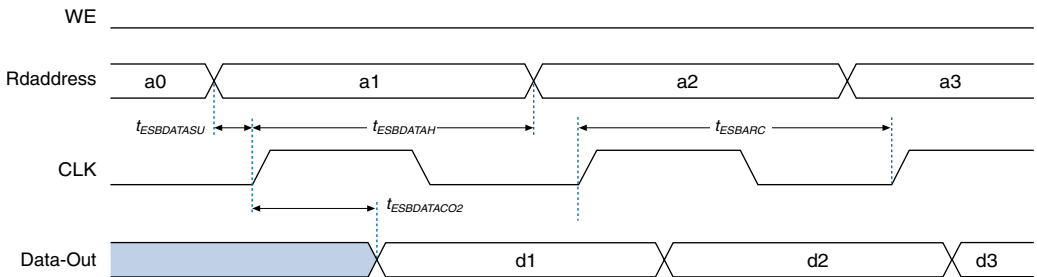
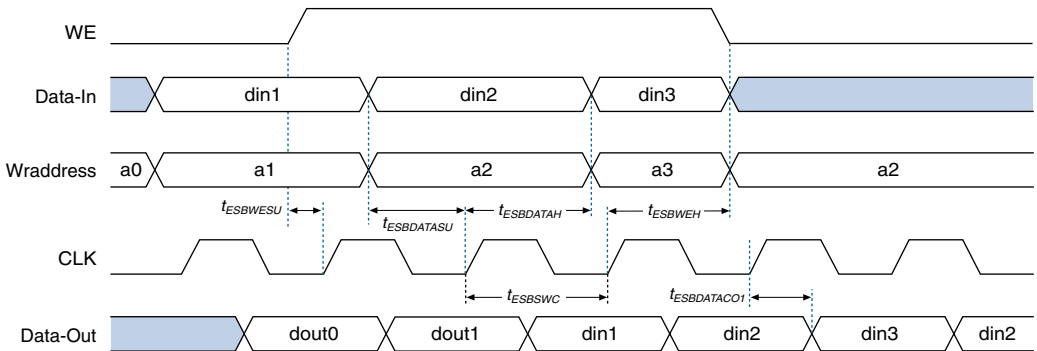
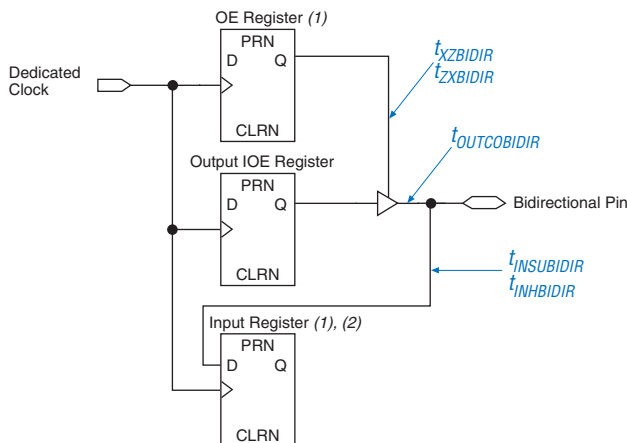
Figure 34. ESB Synchronous Timing Waveforms
ESB Synchronous Read

ESB Synchronous Write (ESB Output Registers Used)


Figure 35 shows the timing model for bidirectional I/O pin timing.

Figure 35. Synchronous Bidirectional Pin External Timing



Notes to Figure 35:

- (1) The output enable and input registers are LE registers in the LAB adjacent to the bidirectional pin. Use the “Output Enable Routing = Single-Pin” option in the Quartus II software to set the output enable register.
- (2) Use the “Decrease Input Delay to Internal Cells = OFF” option in the Quartus II software to set the LAB-adjacent input register. This maintains a zero hold time for LAB-adjacent registers while giving a fast, position-independent setup time. Set “Decrease Input Delay to Internal Cells = ON” and move the input register farther away from the bidirectional pin for a faster setup time with zero hold time. The exact position where zero hold occurs with the minimum setup time varies with device density and speed grade.

Tables 36 to 38 describes the f_{MAX} timing parameters shown in Figure 32. Table 39 describes the functional timing parameters.

Table 36. APEX 20KC t_{MAX} LE Timing Parameters

Symbol	Parameter
t_{SU}	LE register setup time before clock
t_H	LE register hold time before clock
t_{CO}	LE register clock-to-output delay
t_{LUT}	LUT delay for data-in to data-out

Table 49. EP20K200C External Bidirectional Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{\text{INSUBIDIR}}$	1.38		1.78		1.99		ns
t_{INHBIDIR}	0.00		0.00		0.00		ns
$t_{\text{OUTCOBIDIR}}$	2.00	3.79	2.00	4.31	2.00	4.70	ns
t_{XZBIDIR}		6.12		6.51		7.89	ns
t_{ZXBIDIR}		6.12		6.51		7.89	ns
$t_{\text{INSUBIDIRPLL}}$	2.82		3.47		-		ns
$t_{\text{INHBIDIRPLL}}$	0.00		0.00		-		ns
$t_{\text{OUTCOBIDIRPLL}}$	0.50	2.36	0.50	2.62	-	-	ns
$t_{\text{XZBIDIRPLL}}$		4.69		4.82		-	ns
$t_{\text{ZXBIDIRPLL}}$		4.69		4.82		-	ns

Table 50. EP20K400C t_{MAX} LE Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.01		0.01		0.01		ns
t_{H}	0.10		0.10		0.10		ns
t_{CO}		0.27		0.30		0.32	ns
t_{LUT}		0.65		0.78		0.92	ns

Table 61. EP20K600C External Bidirectional Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{\text{INSUBIDIR}}$	2.03		2.57		2.97		ns
t_{INHBIDIR}	0.00		0.00		0.00		ns
$t_{\text{OUTCOBIDIR}}$	2.00	4.29	2.00	4.77	2.00	5.11	ns
t_{XZBIDIR}		8.31		9.14		9.76	ns
t_{ZXBIDIR}		8.31		9.14		9.76	ns
$t_{\text{INSUBIDIRPLL}}$	3.99		4.77		-		ns
$t_{\text{INHBIDIRPLL}}$	0.00		0.00		-		ns
$t_{\text{OUTCOBIDIRPLL}}$	0.50	2.37	0.50	2.63	-	-	ns
$t_{\text{XZBIDIRPLL}}$		6.35		6.94		-	ns
$t_{\text{ZXBIDIRPLL}}$		6.35		6.94		-	ns

Table 62. EP20K1000C t_{MAX} LE Timing Microparameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.01		0.01		0.01		ns
t_{H}	0.10		0.10		0.10		ns
t_{CO}		0.27		0.30		0.32	ns
t_{LUT}		0.66		0.79		0.92	ns

Table 69. Selectable I/O Standard Output Delays

Symbol	-7 Speed Grade		-8 Speed Grad		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min
LVC MOS		0.00		0.00		0.00	ns
LVTTL		0.00		0.00		0.00	ns
2.5 V		0.00		0.00		0.00	ns
1.8 V		1.18		1.41		1.57	ns
PCI		−0.52		−0.53		−0.56	ns
GTL+		−0.18		−0.29		−0.39	ns
SSTL-3 Class I		−0.67		−0.71		−0.75	ns
SSTL-3 Class II		−0.67		−0.71		−0.75	ns
SSTL-2 Class I		−0.67		−0.71		−0.75	ns
SSTL-2 Class II		−0.67		−0.71		−0.75	ns
LVDS		−0.69		−0.70		−0.73	ns
CTT		0.00		0.00		0.00	ns
AGP		0.00		0.00		0.00	ns

Power Consumption

To estimate device power consumption, use the interactive power estimator on the Altera web site at <http://www.altera.com>.

Configuration & Operation

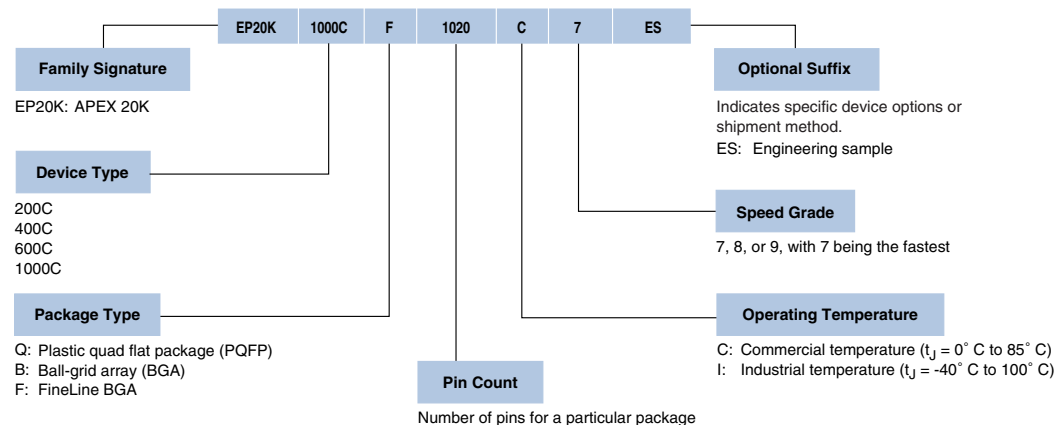
The APEX 20KC architecture supports several configuration schemes. This section summarizes the device operating modes and available device configuration schemes.

Operating Modes

The APEX architecture uses SRAM configuration elements that require configuration data to be loaded each time the circuit powers up. The process of physically loading the SRAM data into the device is called configuration. During initialization, which occurs immediately after configuration, the device resets registers, enables I/O pins, and begins to operate as a logic device. The I/O pins are tri-stated during power-up, and before and during configuration. Together, the configuration and initialization processes are called *command mode*; normal device operation is called *user mode*.

Before and during device configuration, all I/O pins are pulled to V_{CCIO} by a built-in weak pull-up resistor.

Figure 39. APEX 20KC Device Packaging Ordering Information



Revision History

The information contained in the *APEX 20KC Programmable Logic Device Data Sheet* version 2.2 supersedes information published in previous versions.

Version 2.2

The following changes were made to the *APEX 20KC Programmable Logic Device Data Sheet* version 2.2:

- Updated [Tables 1](#).
- Updated notes in [Tables 20](#).

Version 2.1

The following changes were made to the *APEX 20KC Programmable Logic Device Data Sheet* version 2.1:

- Removed figure on AC Test Conditions.
- Updated conditions in [Tables 40](#) and [41](#).
- Added [Tables 42](#) and [43](#).
- Updated V_{OD} in [Table 27](#).
- Added [Figures 36](#) through [38](#).
- Updated [Tables 44](#) through [49](#).
- Updated [Tables 62](#) through [67](#).
- Removed notes in [Tables 44](#) through [67](#).
- Various textual changes throughout the document.